File   View   Edit   Tools   Window   Help

- S6: (1) "9213802"
- S12: (1) "09213802"
- S13: (1) "11168199"
- S14: (7374) transistor and ((interlayer near2 (insulat$
- S15: (1356) S14 and (second adj gate)
- S16: (152) S15 and (second adj (sidewall or (side adj wa
- S17: (137) S16 and (conduct$4)
- S18: (3) S17 and ((driv$4 or control$4) near2 transisto
- S19: (3) Backward citation search 7
- S20: (20) Forward citation search 6
- S22: (101) S17 not (S18 S19 S20)
- S23: (101) S22 and (second adj (sidewall or (side adj wa
- S24: (2) S23 and (compress$4)
- S25: (0) S23 and (silicide and nitride and plug)
- S26: (38) S23 and (silicide and nitride and plug)
- S27: (104) ((driv$4 or control$4) near2 transistor) and
- S28: (55) S27 and ((side adj wall) or sidewall or space
- S29: (54) S28 not (S3 S4 S5 S24 S26 S18 S19 S20)
- S30: (53) S29 and (source and drain and substrate)

S17 and ((driv$# or control$4) near2 transistor)

	U		PT	P	Document ID	Issue Date	Pages	Title	A	Current OR	Curr
1	☐	☐	☐	☐	US 20050051772 A1	20050310	34	Semiconductor device and method of manufacturing the same		257/59	257/3 257/4
2	☐	☐	☐	☐	US 20050041505 A1	20050224	67	Ferroelectric memory and method for manufacturing the same		365/222	
3	☐	☐	☐	☐	US 20040232511 A1	20041125	22	Semiconductor device and method of manufacturing the same		257/500	
4	☐	☐	☐	☐	US 20040203207 A1	20041014	31	Semiconductor device and method of manufacturing the same		438/258	257/E 257/E
5	☐	☐	☐	☐	US 20040026740 A1	20040212	32	Semiconductor device and a method of manufacturing the same		257/380	257/E
6	☐	☐	☐	☐	US 20030227049 A1	20031211	31	Non-volatile semiconductor memory device		257/315	257/E 257/E
7	☐	☐	☐	☐	US 20030222294 A1	20031204	37	Nonvolatile semiconductor storage device		257/298	257/E 257/E
8	☐	☐	☐	☐	US 20030203572 A1	20031030	41	Nonvolatile semiconductor memory device and its manufacturing method		438/257	257/3 257/E
9	☐	☐	☐	☐	US 20030022422 A1	20030130	28	Semiconductor device and its manufacturing method		438/183	257/E
10	☐	☐	☐	☐	US 20020127793 A1	20020912	43	Semiconductor device and its manufacture method		438/201	257/3 257/E
11	☐	☐	☐	☐	US 20020045311 A1	20020418	70	Ferroelectric memory and method for manufacturing the same		438/240	257/E 257/E

Ready

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S1	1	"20040178516"	US-PGPUB; USPAT; EPO; JPO; IBM_TDB	OR	ON	2005/03/11 12:36
S2	18	ogata-tamotsu.in.	US-PGPUB; USPAT; EPO; JPO; IBM_TDB	OR	ON	2005/03/11 12:37
S3	1	"20040178516"	US-PGPUB; USPAT; EPO; JPO; IBM_TDB	OR	ON	2005/03/11 16:47
S4	18	ogata-tamotsu.in.	US-PGPUB; USPAT; EPO; JPO; IBM_TDB	OR	ON	2005/03/11 16:47
S5	7	S4 and transistor and (hole or open$4) and gate and substrate	US-PGPUB; USPAT; EPO; JPO; IBM_TDB	OR	ON	2005/03/11 16:50
S6	1	"9213802"	US-PGPUB; USPAT; EPO; JPO; IBM_TDB	OR	ON	2005/03/11 16:51
S12	1	"09213802"	US-PGPUB; USPAT; EPO; JPO; IBM_TDB	OR	ON	2005/03/11 16:53
S13	1	"11168199"	US-PGPUB; USPAT; EPO; JPO; IBM_TDB	OR	ON	2005/03/11 16:56
S14	7374	transistor and ((interlayer near2 (insulat$4 or dielectric)) or (interdielectric or interinsulat$4 or inter-dielectric or inter-insulat$4 or (inter adj (dielectric or insulati$4)))) and (open$4 or hole) and source and drain and gate and (sidewall or (side adj wall) or spacer)	US-PGPUB; USPAT; EPO; JPO; IBM_TDB	OR	ON	2005/03/11 17:00
S15	1356	S14 and (second adj gate)	US-PGPUB; USPAT; EPO; JPO; IBM_TDB	OR	ON	2005/03/11 17:00
S16	152	S15 and (second adj (sidewall or (side adj wall) or spacer))	US-PGPUB; USPAT; EPO; JPO; IBM_TDB	OR	ON	2005/03/11 17:01
S17	137	S16 and (conduct$4)	US-PGPUB; USPAT; EPO; JPO; IBM_TDB	OR	ON	2005/03/11 17:02
S18	36	S17 and ((driv$4 or control$4) near2 transistor)	US-PGPUB; USPAT; EPO; JPO; IBM_TDB	OR	ON	2005/03/11 18:14
S19	3	("4305200" | "4925807" | "5061975").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2005/03/11 17:53
S20	20	("5621232").URPN.	USPAT	OR	ON	2005/03/11 17:56
S22	101	S17 not (S18 S19 S20)	US-PGPUB; USPAT; EPO; JPO; IBM_TDB	OR	ON	2005/03/11 18:04

S23	101	S22 and (second adj (sidewall or (side adj wall) or spacer))	US-PGPUB; USPAT; EPO; JPO; IBM_TDB	OR	ON	2005/03/11 18:04
S24	2	S23 and (compress$4)	US-PGPUB; USPAT; EPO; JPO; IBM_TDB	OR	ON	2005/03/11 18:05
S25	0	S23 and (cilicide and nitride and plug)	US-PGPUB; USPAT; EPO; JPO; IBM_TDB	OR	ON	2005/03/11 18:07
S26	38	S23 and (silicide and nitride and plug)	US-PGPUB; USPAT; EPO; JPO; IBM_TDB	OR	ON	2005/03/11 18:14
S27	104	((driv$4 or control$4) near2 transistor) and (load adj transistor) and gate and ((interlayer near2 (insulat$4 or dielectric)) or interdielectric or interinsulat$4 or inter-dielectric or inter-insulat$4 or (inter adj (dielectric or insulati$4))) and plug	US-PGPUB; USPAT; EPO; JPO; IBM_TDB	OR	ON	2005/03/11 18:16
S28	55	S27 and ((side adj wall) or sidewall or spacer)	US-PGPUB; USPAT; EPO; JPO; IBM_TDB	OR	ON	2005/03/11 18:17
S29	54	S28 not (S3 S4 S5 S24 S26 S18 S19 S20)	US-PGPUB; USPAT; EPO; JPO; IBM_TDB	OR	ON	2005/03/11 18:17
S30	53	S29 and (source and drain and substrate)	US-PGPUB; USPAT; EPO; JPO; IBM_TDB	OR	ON	2005/03/11 18:18
S31	40	S30 and gate and nitride and oxide	US-PGPUB; USPAT; EPO; JPO; IBM_TDB	OR	ON	2005/03/11 18:25
S32	13	S30 not S31	US-PGPUB; USPAT; EPO; JPO; IBM_TDB	OR	ON	2005/03/11 18:25